L Number	Hits	Search Text	DB	Time stamp
1	4034	memory adj2 cell$1 and contact adj2 hole$1 and transistor$1 and bit adj2 line$2	USPAT; EPO; JPO; DERWENT	2004/09/24 16:36
2	711	(memory adj2 cell$1 and contact adj2 hole$1 and transistor$1 and bit adj2 line$2) and gate and nonvolatile	USPAT; EPO; JPO; DERWENT	2004/09/24 16:37
3	4944	nonvolatile adj2 semiconductor near5 memory	USPAT; EPO; JPO; DERWENT	2004/09/24 16:38
4	3312	(nonvolatile adj2 semiconductor near5 memory) and memory adj cell$1	USPAT; EPO; JPO; DERWENT	2004/09/24 16:38
5	373	((nonvolatile adj2 semiconductor near5 memory) and memory adj cell$1) and contact near5 hole	USPAT; EPO; JPO; DERWENT	2004/09/24 16:38
6	130	(((nonvolatile adj2 semiconductor near5 memory) and memory adj cell$1) and contact near5 hole) and metal near5 (wiring or line) and transistor	USPAT; EPO; JPO; DERWENT	2004/09/24 16:39